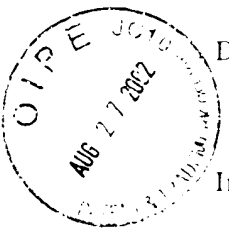


CP 2823



DOCKET: CU-2636

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application: Sang Ick LEE et al.]
Serial No: 09/994,284]
Filed: November 26, 2001]
For: METHOD OF FORMING METAL]
GATE IN SEMICONDUCTOR]
DEVICE]

GRP ART UNIT: 2823

Ex.: T. V. Pham

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Certification under 37 C.F.R. §1.8(a)

I hereby certify that this paper (along with any paper referred to as being attached or enclosed) is being deposited with The United States Postal Service with sufficient postage as first class mail in an envelope addressed to The Commissioner for Patents, Washington, D.C. 20231 on August 21, 2002.

Vangelis Economou
Vangelis Economou, Reg. No. 32,341

Commissioner for Patents
Washington, D.C. 20231

AMENDMENT

In response to the Office Action dated May 23, 2002, setting a 3-month shortened statutory period for a reply ending on August 23, 2002, the Applicants submit the following responsive amendment in the above-identified application. The Applicants believe that this amendment places the application in better condition for allowance.